



# DATA SHEET

SEMICONDUCTOR

1N4448



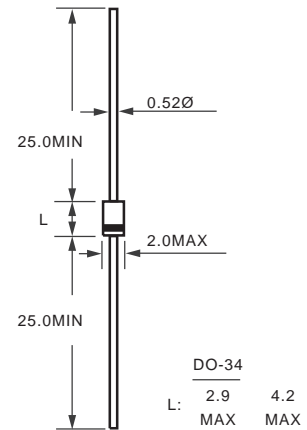
## FEATURES

- \* Silicon epitaxial planar diodes
- \* Low power loss, high efficiency
- \* Low leakage
- \* Low forward voltage
- \* High speed switching
- \* High current capability
- \* High reliability

## MECHANICAL DATA

- \* Case: Glass sealed case
- \* Lead: MIL-STD-202E, Method 208 guaranteed
- \* Polarity: Color band denotes cathode end
- \* Mounting position: Any
- \* Weight: 0.13 gram

DO-35



Dimensions in millimeters

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

	SYMBOL	1N4448	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	100	V
Maximum Average Rectified Current	Io	150	mA
Maximum Power Dissipation Tamb=25°C	Ptot	500	mW
Maximum Forward Voltage	VF	1.0/100	V/mA
Maximum Reverse Current	IR	5000/75	nA/V
Maximum Reverse Recovery Time	trr	4.0	nS
Typical Junction Capacitance	CJ	4.0	pF
Operating and Storage Temperature Range	TJ,TSTG	-65 to + 200	°C

NOTE: 1-1N914A, 1N914B IS SAME AS 1N914, EXCEPT DIFFERENT IN FORWARD VOLTAGE:

- 1N914A-1.0/20 V/mA
- 1N914B-1.0/100 V/mA

2.Suffix "M" stands for "DO-34" package.(e.g.:1N4148M)

# DEVICE CHARACTERISTICS

## 1N4448

